

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2816423	diagram or membrane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 10:11
S2	859723	cavity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:14
S3	145590	S1 and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 14:10
S4	2128	nano\$pore or nano\$1porous or nano\$1porosity or nano\$1hole	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:18
S5	2994	(nano\$1scal\$3 or molecular\$scal\$3 or microscal\$3) near7 (pore or hole or device or structure or apparatus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:16
S6	155505	(nano\$1meter or nano or nano\$1metre or micro\$1meter or micro\$1metre or micro\$1) near10 (pore or porous or porosity or hole or device or structure or apparatus)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:17
S7	157910	S4 or S5 or S6	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 14:22
S8	8519	S3 and S7	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 14:23

S9	532	S3 and (S4 or S5)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 14:30
S10	3934225	semiconductor or silicon or si	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 10:11
S11	442	S9 and S10	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:11
S12	1	"6413792".PN.	USPAT; USOCR	OR	ON	2005/04/14 16:38
S13	1	"6428959".PN.	USPAT; USOCR	OR	ON	2005/04/14 16:38
S14	1	"20030013186".PN.	US-PGPUB	OR	ON	2005/04/14 16:39
S15	22527	micro\$fluid\$3 or micro adj3 (fluid\$3 or channel) or micro\$1channel	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:14
S16	2816423	diagram or membrane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:14
S17	859723	cavity	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:14
S18	3934225	semiconductor or silicon or si	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:15

S19	1419	S15 and S16 and S17 and S18	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:15
S20	3003	(nano\$1scal\$3 or molecular\$scal\$3 or microscal\$3) near7 (pore or hole or device or structure or apparatus or aperture)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:16
S21	151107	(nano\$1meter or nano or nano\$1metre or micro\$1meter or micro\$1metre or micro\$1) near10 (pore or hole or device or structure or apparatus or aperture)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:17
S22	438	nano\$pore or nano\$1hole or nano\$1aperture	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/14 17:18
S23	710	S19 and (S20 or S21 or S22)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 09:57
S24	2788	(257/414 or 257/419 or 257/619 or 438/53 or 438/928 or 438/977).ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 10:11
S25	2816423	diagram or membrane	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 10:11
S26	913	S24 and S25	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 10:11

S27	3934225	semiconductor or silicon or si	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 10:12
S28	881	S26 and S27	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/15 10:12
S29	2	("6464842").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/04/15 11:23